

REJ03G1841-0100

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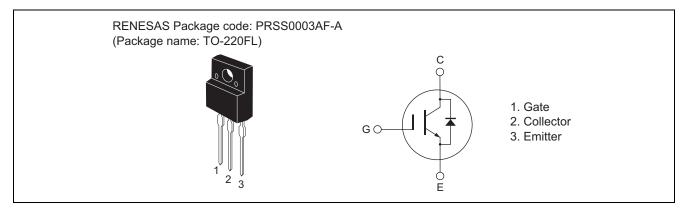
RJH60D2DPP-M0

Silicon N Channel IGBT Application: Inverter

Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

	Item	Symbol	Ratings	Unit	
Collector to emitter voltage / diode reverse voltage		V _{CES} / V _R	600	V	
Gate to emitter voltage		V _{GES}	±30	V	
Collector current	Tc = 25°C	lc	20	А	
	Tc = 100°C	lc	10	А	
Collector peak current		ic(peak) Note1	40	А	
Collector to emitter diode forward current		i _{DF}	10	А	
Collector to emitter diode forward peak current		i _{DF} (peak) ^{Note1}	40	А	
Collector dissipation		P _C ^{Note2}	22.5	W	
Junction to case thermal impedance		θj-c ^{Note2}	5.5	°C/W	
Junction temperature		Tj	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

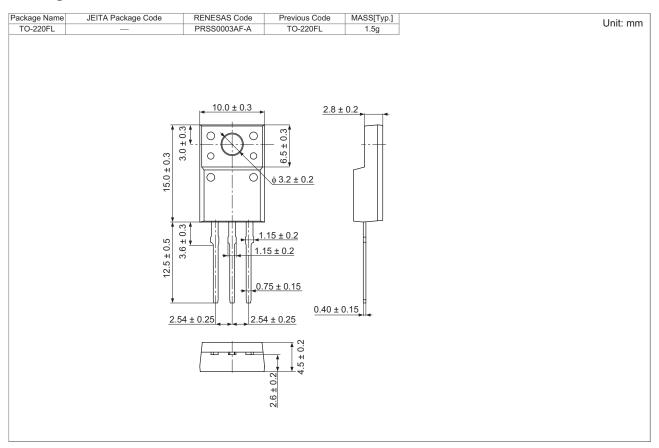
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions	
Zero gate voltage collector current	I _{CES} / I _R	_	_	100	μA	V _{CE} = 600 V, V _{GE} = 0	
/ Diode reverse current							
Gate to emitter leak current	I _{GES}	—	—	±1	μA	$V_{GE} = \pm 30 \text{ V}, \text{ V}_{CE} = 0$	
Gate to emitter cutoff voltage	V _{GE(off)}	4.0	_	6.0	V	V_{CE} = 10 V, I_{C} = 1 mA	
Collector to emitter saturation voltage	V _{CE(sat)}	_	1.6	2.2	V	I_{C} = 10 A, V_{GE} = 15 V ^{Note3}	
	V _{CE(sat)}	_	1.8	_	V	I_{C} = 20 A, V_{GE} = 15 V ^{Note3}	
Input capacitance	Cies	_	430	_	pF	V _{CE} = 25 V	
Output capacitance	Coes	_	35	_	pF	V _{GE} = 0	
Reveres transfer capacitance	Cres	_	15	_	pF	f = 1 MHz	
Total gate charge	Qg	_	19.1	_	nC	V _{GE} = 15 V V _{CE} = 300 V	
Gate to emitter charge	Qge	_	3.0	_	nC		
Gate to collector charge	Qgc	_	9.0	_	nC	I _C = 10A	
Switching time	t _{d(on)}	_	30	_	ns	I _C = 10 A	
	tr	_	30	_	ns	R _L = 30 Ω V _{GE} = 15 V Rg = 5 Ω	
	t _{d(off)}		50		ns		
	t _f	_	90	_	ns		

FRD Forward voltage	V_{F}		1.8	2.3	V	$I_F = 10 A^{Note3}$
FRD reverse recovery time	trr	—	100		ns	I _F = 10 A
						di _F /dt = 100 A/µs

Notes: 3. Pulse test.

4. Under development — The specifications potentially be changed without notice.

Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJH60D2DPP-M0-T2	1050 pcs	Box (Tube)

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